Part Number	Customer

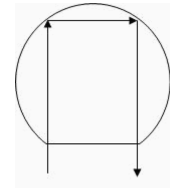
Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm	Customer supplied material
	2.0	Notch or Flat	Notch	Customer supplied material
	3.0	Notch Direction	{110} +/- 1 degree	Customer supplied material
	4.0	Overall Thickness	611.00 +/- 11.00 µm	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	6.0	Bow	<80.00µm	ADE 100%, SEMI MF1530
	7.0	Warp	<80.00µm	ADE 100%, SEMI MF1530
	8.0	Edge Chips	none	Bright Light, 100%
	9.0	Edge Exclusion	5mm	
HandleSilicon	10.0	Handle Growth Method	CZ	Customer supplied material
	11.0	Handle Orientation	{100} +/- 0.5 degree	Customer supplied material
	12.0	Handle Thickness	600.00 +/- 10.00 µm	ADE, 100%
	13.0	Handle Doping Type	P	Customer supplied material
	14.0	Handle Dopant	Boron	Customer supplied material
	15.0	Handle Resistivity	<0.019 Ohm-cm	Customer supplied material
	16.0	Backside Finish	Polished with oxide and laser mark	Guaranteed by process
BuriedOxide	17.0	Oxide Type	Thermal	
	18.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	19.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	20.0	Device Orientation	{100} +/- 0.5 degree	Customer supplied material
	21.0	Nominal Thickness	10.00 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	23.0	Device Doping Type	P	Customer supplied material
	24.0	Device Dopant	Boron	Customer supplied material
	25.0	Device Growth Method	CZ	Customer supplied material
	26.0	Device Resistivity	<0.019 Ohm-cm	Customer supplied material
	27.0	Voids	none	Bright Light, 100% (note 2)
	28.0	Scratches	Frontside - no scratches allowed. Backside - light handling marks	Bright Light, 100% (note 2)
	29.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

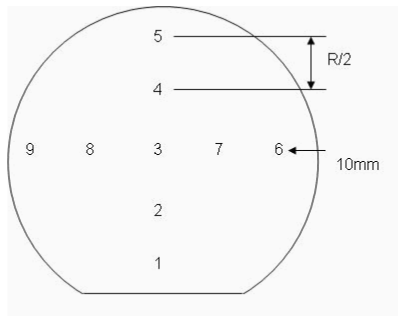
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information